

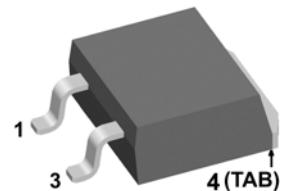
Standard Rectifier

V_{RRM} = 1600V
 I_{FAV} = 30A
 V_F = 1.26V

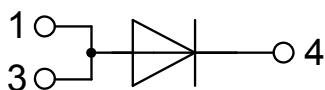
Single Diode

Part number

DMA30IM1600PZ



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

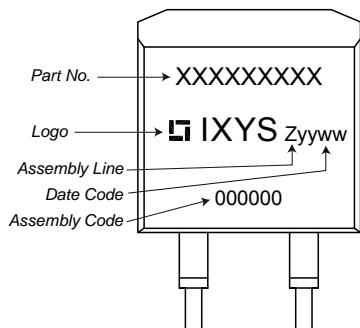
Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_R	reverse current	$V_R = 1600 V$ $V_R = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		40 1.5	μA mA
V_F	forward voltage drop	$I_F = 30 A$ $I_F = 60 A$ $I_F = 30 A$ $I_F = 60 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.29 1.60 1.26 1.65	V V
I_{FAV}	average forward current	$T_C = 140^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ C$		30	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		0.82 14.1	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.7	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		210	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		300 325 255 275	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 150^\circ C$ $V_R = 0 V$		450 440 325 315	A^2s A^2s A^2s A^2s
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		10	pF

Package TO-263 (D2Pak-HV)

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				1.5		g
F_c	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/Abp}$		terminal to backside	4.7			mm

Product Marking



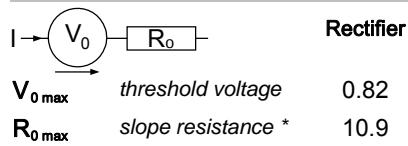
Part number

D = Diode
M = Standard Rectifier
A = (up to 1800V)
30 = Current Rating [A]
IM = Single Diode
1600 = Reverse Voltage [V]
PZ = TO-263AB (D2Pak) (2HV)

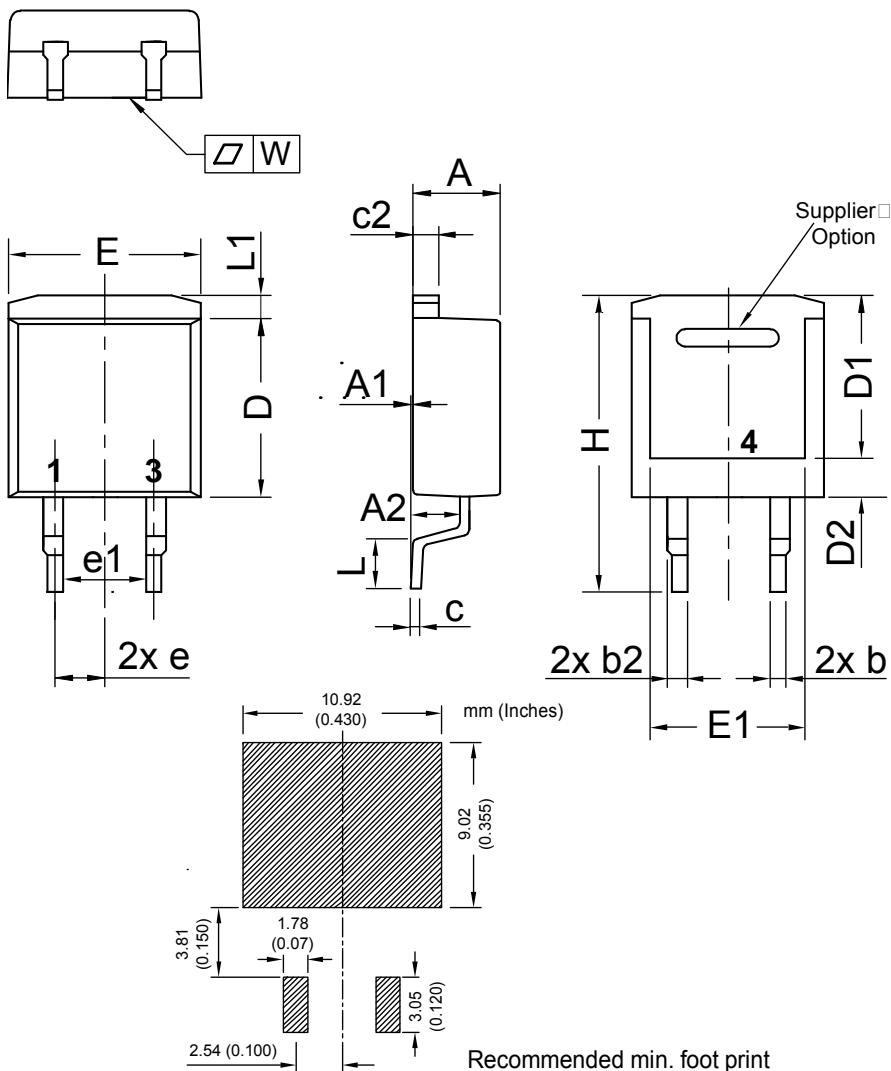
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA30IM1600PZ	DMA30IM1600PZ	Tape & Reel	800	515813

Equivalent Circuits for Simulation

* on die level

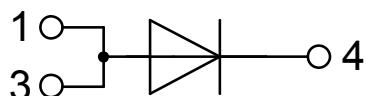
 $T_{VJ} = 175 \text{ }^{\circ}\text{C}$ 

Outlines TO-263 (D2Pak-HV)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with
and/or within JEDEC standard.



Rectifier

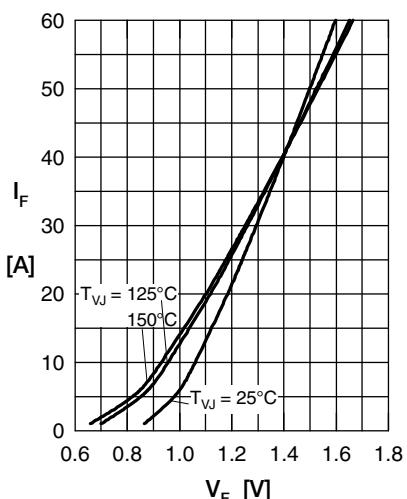


Fig. 1 Forward current versus voltage drop per diode

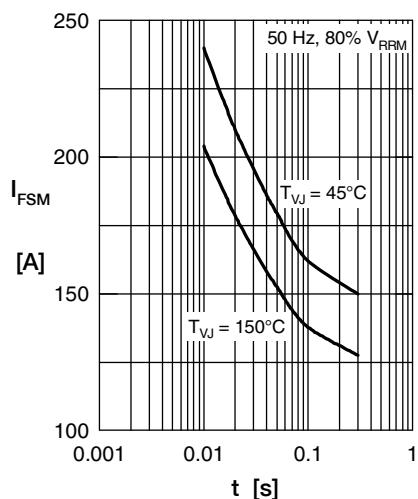


Fig. 2 Surge overload current

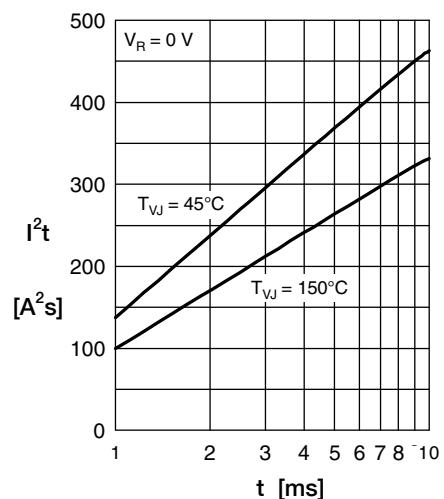
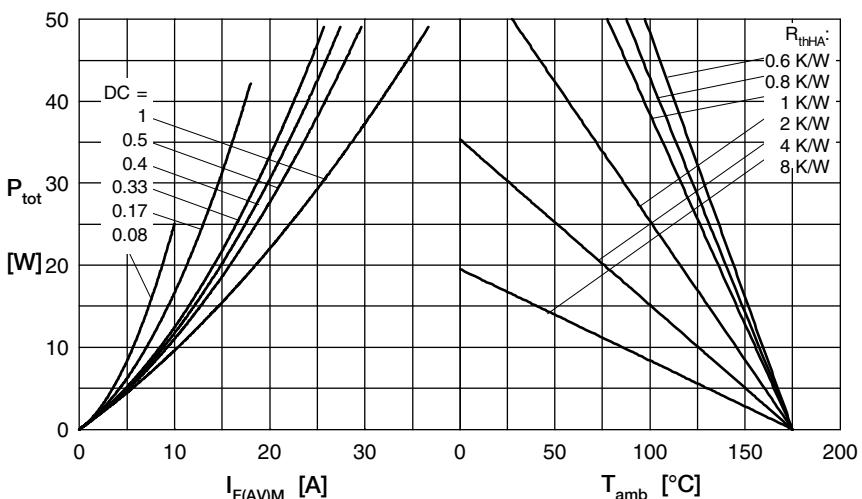
Fig. 3 I^2t versus time per diode

Fig. 4 Power dissipation vs. direct output current and ambient temperature

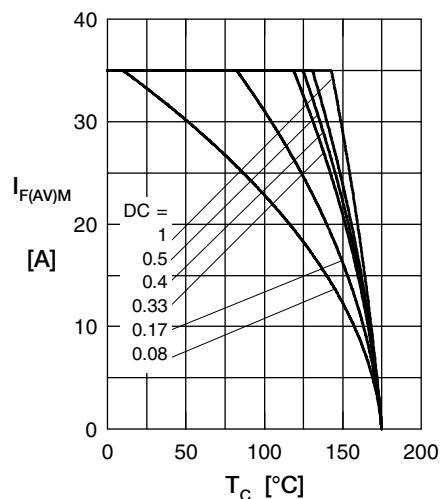


Fig. 5 Max. forward current vs. case temperature

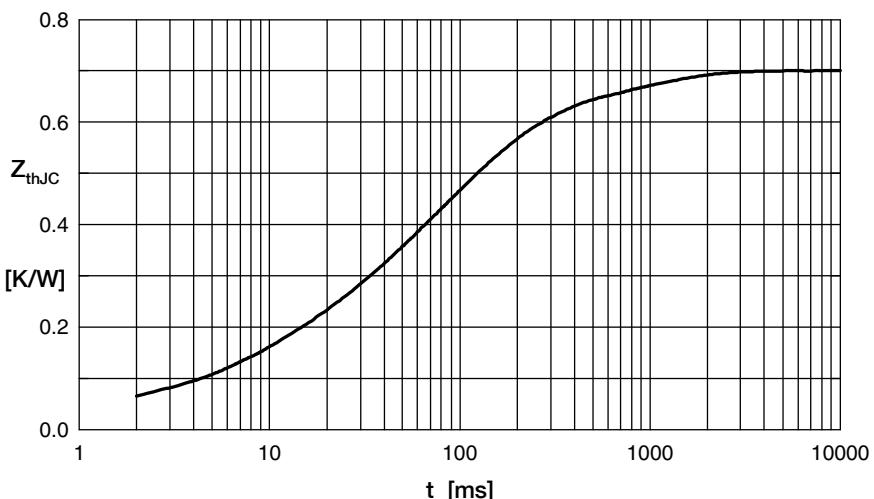


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.03	0.0003
2	0.072	0.0065
3	0.131	0.027
4	0.367	0.105
5	0.1	0.8